

**Abstract**

[lacuna] for limiting overcurrents by means of a semiconductor element (1) having at least one controllable semiconductor (3) having an electron source (source), an electron sink (drain) and a control electrode (gate) which controls the flow of electrons, which semiconductor has characteristic curves after the manner of a field-effect transistor (FET;3). Two FETs are reverse-connected in series in the case of AC voltage. Means are provided for internally obtaining the control voltage required for driving the semiconductor element (1) from at least part of the load current and/or from at least part of the voltage drop across the semiconductor element.

FIG 1